



# STD1NB60

## N - CHANNEL 600V - 7.4Ω - 1A - IPAK/DPAK PowerMESH™ MOSFET

PRELIMINARY DATA

| TYPE     | V <sub>DSS</sub> | R <sub>DS(on)</sub> | I <sub>D</sub> |
|----------|------------------|---------------------|----------------|
| STD1NB60 | 600 V            | < 8.5 Ω             | 1 A            |

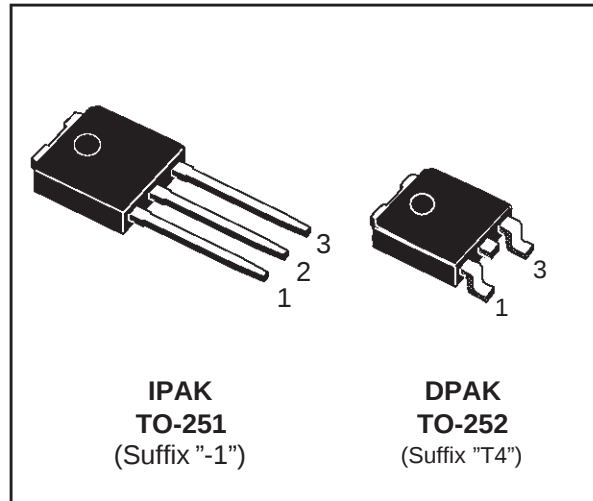
- TYPICAL R<sub>DS(on)</sub> = 7.4 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

### DESCRIPTION

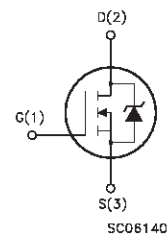
Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R<sub>DS(on)</sub> per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

### APPLICATIONS

- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

| Symbol              | Parameter                                             | Value      | Unit |
|---------------------|-------------------------------------------------------|------------|------|
| V <sub>DS</sub>     | Drain-source Voltage (V <sub>GS</sub> = 0)            | 600        | V    |
| V <sub>DGR</sub>    | Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)         | 600        | V    |
| V <sub>GS</sub>     | Gate-source Voltage                                   | ± 30       | V    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>c</sub> = 25 °C  | 1          | A    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>c</sub> = 100 °C | 0.63       | A    |
| I <sub>DM</sub> (•) | Drain Current (pulsed)                                | 4          | A    |
| P <sub>tot</sub>    | Total Dissipation at T <sub>c</sub> = 25 °C           | 45         | W    |
|                     | Derating Factor                                       | 0.36       | W/°C |
| dv/dt(1)            | Peak Diode Recovery voltage slope                     | 3.5        | V/ns |
| T <sub>stg</sub>    | Storage Temperature                                   | -65 to 150 | °C   |
| T <sub>j</sub>      | Max. Operating Junction Temperature                   | 150        | °C   |

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 1 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

## STD1NB60

### THERMAL DATA

|                |                                                |     |      |               |
|----------------|------------------------------------------------|-----|------|---------------|
| $R_{thj-case}$ | Thermal Resistance Junction-case               | Max | 2.78 | $^{\circ}C/W$ |
| $R_{thj-amb}$  | Thermal Resistance Junction-ambient            | Max | 100  | $^{\circ}C/W$ |
| $R_{thc-sink}$ | Thermal Resistance Case-sink                   | Typ | 1.5  | $^{\circ}C/W$ |
| $T_I$          | Maximum Lead Temperature For Soldering Purpose |     | 275  | $^{\circ}C$   |

### AVALANCHE CHARACTERISTICS

| Symbol   | Parameter                                                                                        | Max Value | Unit |
|----------|--------------------------------------------------------------------------------------------------|-----------|------|
| $I_{AR}$ | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max)               | 1         | A    |
| $E_{AS}$ | Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$ , $I_D = I_{AR}$ , $V_{DD} = 50 V$ ) | 150       | mJ   |

### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

#### OFF

| Symbol        | Parameter                                        | Test Conditions                                                                   | Min. | Typ. | Max.      | Unit               |
|---------------|--------------------------------------------------|-----------------------------------------------------------------------------------|------|------|-----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source Breakdown Voltage                   | $I_D = 250 \mu A$ $V_{GS} = 0$                                                    | 600  |      |           | V                  |
| $I_{DSS}$     | Zero Gate Voltage Drain Current ( $V_{GS} = 0$ ) | $V_{DS} = \text{Max Rating}$<br>$V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$ |      |      | 1<br>10   | $\mu A$<br>$\mu A$ |
| $I_{GSS}$     | Gate-body Leakage Current ( $V_{DS} = 0$ )       | $V_{GS} = \pm 30 V$                                                               |      |      | $\pm 100$ | nA                 |

#### ON (\*)

| Symbol       | Parameter                         | Test Conditions                                              | Min. | Typ. | Max. | Unit     |
|--------------|-----------------------------------|--------------------------------------------------------------|------|------|------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}$ $I_D = 250 \mu A$                          | 3    | 4    | 5    | V        |
| $R_{DS(on)}$ | Static Drain-source On Resistance | $V_{GS} = 10V$ $I_D = 0.6 A$                                 |      | 7.4  | 8.5  | $\Omega$ |
| $I_{D(on)}$  | On State Drain Current            | $V_{DS} > I_{D(on)} \times R_{DS(on)max}$<br>$V_{GS} = 10 V$ | 1    |      |      | A        |

### DYNAMIC

| Symbol                              | Parameter                                                               | Test Conditions                                       | Min. | Typ.             | Max. | Unit           |
|-------------------------------------|-------------------------------------------------------------------------|-------------------------------------------------------|------|------------------|------|----------------|
| $g_{fs} (*)$                        | Forward Transconductance                                                | $V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1 A$ |      | 0.97             |      | S              |
| $C_{iss}$<br>$C_{oss}$<br>$C_{rss}$ | Input Capacitance<br>Output Capacitance<br>Reverse Transfer Capacitance | $V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$              |      | 180<br>32<br>3.5 |      | pF<br>pF<br>pF |

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

| Symbol      | Parameter          | Test Conditions                                                   | Min. | Typ. | Max. | Unit |
|-------------|--------------------|-------------------------------------------------------------------|------|------|------|------|
| $t_{d(on)}$ | Turn-on Time       | $V_{DD} = 300\text{ V}$ $I_D = 0.5\text{ A}$                      |      | 13   |      | ns   |
| $t_r$       | Rise Time          | $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$                        |      | 15   |      | ns   |
| $Q_g$       | Total Gate Charge  | $V_{DD} = 480\text{ V}$ $I_D = 1\text{ A}$ $V_{GS} = 10\text{ V}$ |      | 7    | 10   | nC   |
| $Q_{gs}$    | Gate-Source Charge |                                                                   |      | 2    |      | nC   |
| $Q_{gd}$    | Gate-Drain Charge  |                                                                   |      | 3.5  |      | nC   |

**SWITCHING OFF**

| Symbol        | Parameter             | Test Conditions                            | Min. | Typ. | Max. | Unit |
|---------------|-----------------------|--------------------------------------------|------|------|------|------|
| $t_{r(Voff)}$ | Off-voltage Rise Time | $V_{DD} = 480\text{ V}$ $I_D = 1\text{ A}$ |      | 27   |      | ns   |
| $t_f$         | Fall Time             | $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ |      | 32   |      | ns   |
| $t_c$         | Cross-over Time       |                                            |      | 35   |      | ns   |

**SOURCE DRAIN DIODE**

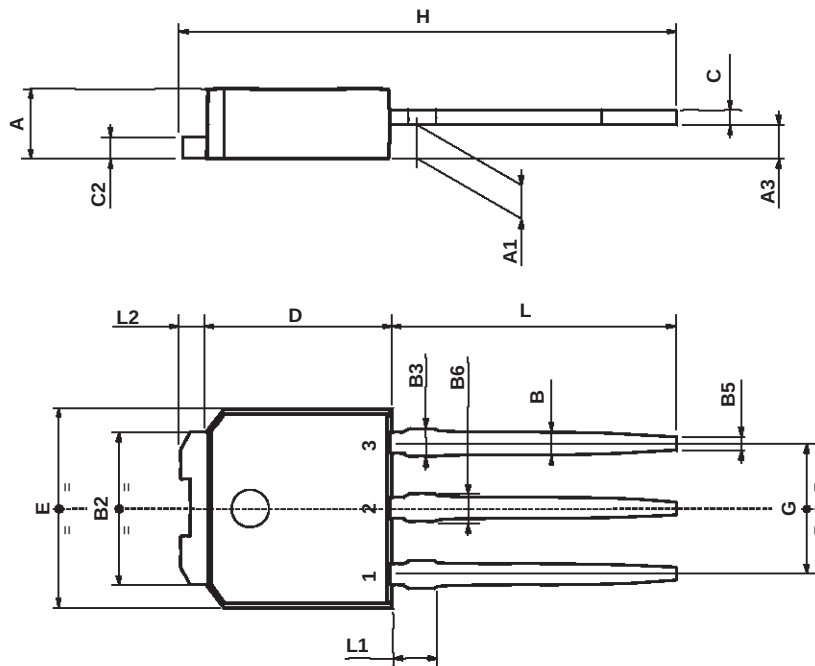
| Symbol             | Parameter                     | Test Conditions                                                                                                       | Min. | Typ. | Max. | Unit |
|--------------------|-------------------------------|-----------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| $I_{SD}$           | Source-drain Current          |                                                                                                                       |      |      | 1    | A    |
| $I_{SDM}(\bullet)$ | Source-drain Current (pulsed) |                                                                                                                       |      |      | 4    | A    |
| $V_{SD} (*)$       | Forward On Voltage            | $I_{SD} = 1\text{ A}$ $V_{GS} = 0$                                                                                    |      |      | 1.6  | V    |
| $t_{rr}$           | Reverse Recovery Time         | $I_{SD} = 1\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$<br>$V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ |      | 350  |      | ns   |
| $Q_{rr}$           | Reverse Recovery Charge       |                                                                                                                       |      | 825  |      | nC   |
| $I_{RRM}$          | Reverse Recovery Current      |                                                                                                                       |      | 4.7  |      | A    |

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

TO-251 (IPAK) MECHANICAL DATA

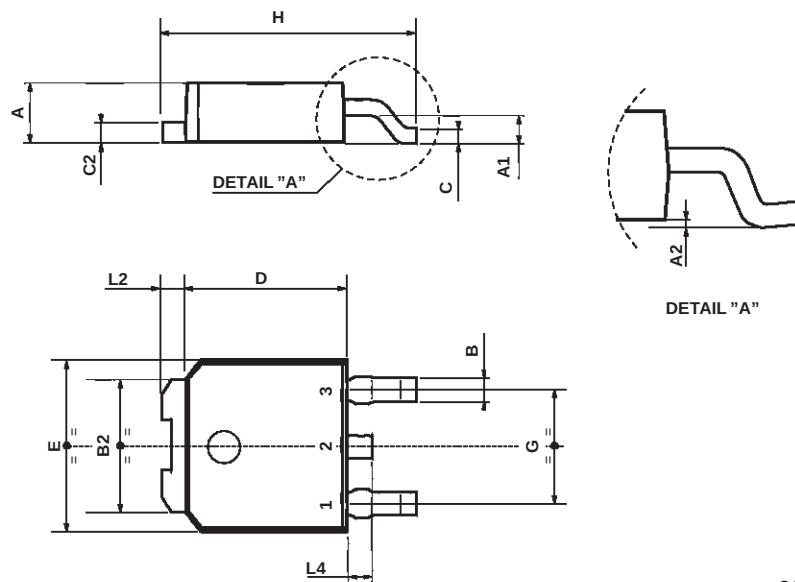
| DIM. | mm   |      |      | inch  |       |       |
|------|------|------|------|-------|-------|-------|
|      | MIN. | TYP. | MAX. | MIN.  | TYP.  | MAX.  |
| A    | 2.2  |      | 2.4  | 0.086 |       | 0.094 |
| A1   | 0.9  |      | 1.1  | 0.035 |       | 0.043 |
| A3   | 0.7  |      | 1.3  | 0.027 |       | 0.051 |
| B    | 0.64 |      | 0.9  | 0.025 |       | 0.031 |
| B2   | 5.2  |      | 5.4  | 0.204 |       | 0.212 |
| B3   |      |      | 0.85 |       |       | 0.033 |
| B5   |      | 0.3  |      |       | 0.012 |       |
| B6   |      |      | 0.95 |       |       | 0.037 |
| C    | 0.45 |      | 0.6  | 0.017 |       | 0.023 |
| C2   | 0.48 |      | 0.6  | 0.019 |       | 0.023 |
| D    | 6    |      | 6.2  | 0.236 |       | 0.244 |
| E    | 6.4  |      | 6.6  | 0.252 |       | 0.260 |
| G    | 4.4  |      | 4.6  | 0.173 |       | 0.181 |
| H    | 15.9 |      | 16.3 | 0.626 |       | 0.641 |
| L    | 9    |      | 9.4  | 0.354 |       | 0.370 |
| L1   | 0.8  |      | 1.2  | 0.031 |       | 0.047 |
| L2   |      | 0.8  | 1    |       | 0.031 | 0.039 |



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## TO-252 (DPAK) MECHANICAL DATA

| DIM. | mm   |      |      | inch  |       |       |
|------|------|------|------|-------|-------|-------|
|      | MIN. | TYP. | MAX. | MIN.  | TYP.  | MAX.  |
| A    | 2.2  |      | 2.4  | 0.086 |       | 0.094 |
| A1   | 0.9  |      | 1.1  | 0.035 |       | 0.043 |
| A2   | 0.03 |      | 0.23 | 0.001 |       | 0.009 |
| B    | 0.64 |      | 0.9  | 0.025 |       | 0.035 |
| B2   | 5.2  |      | 5.4  | 0.204 |       | 0.212 |
| C    | 0.45 |      | 0.6  | 0.017 |       | 0.023 |
| C2   | 0.48 |      | 0.6  | 0.019 |       | 0.023 |
| D    | 6    |      | 6.2  | 0.236 |       | 0.244 |
| E    | 6.4  |      | 6.6  | 0.252 |       | 0.260 |
| G    | 4.4  |      | 4.6  | 0.173 |       | 0.181 |
| H    | 9.35 |      | 10.1 | 0.368 |       | 0.397 |
| L2   |      | 0.8  |      |       | 0.031 |       |
| L4   | 0.6  |      | 1    | 0.023 |       | 0.039 |



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